



BREAKTHROUGH SIMPLICITY

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# Large-signal PHEMT and HBT modeling for power amplifier applications

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# Agenda

- Introduction
- Phemt modeling issues
- Empirical model vs table-based model; Charge model vs 'no-charge' model
- Class-inverse-F operation of power PHEMTs
- Models of III-V-based HBTs
  - Modified GP model
  - VBIC model
  - Modified VBIC model
  - Thermal coupling model
- Small-signal and large-signal HBT model verification
- HBT modeling application to power amplifier

# Challenges of modeling for power amplifier designs

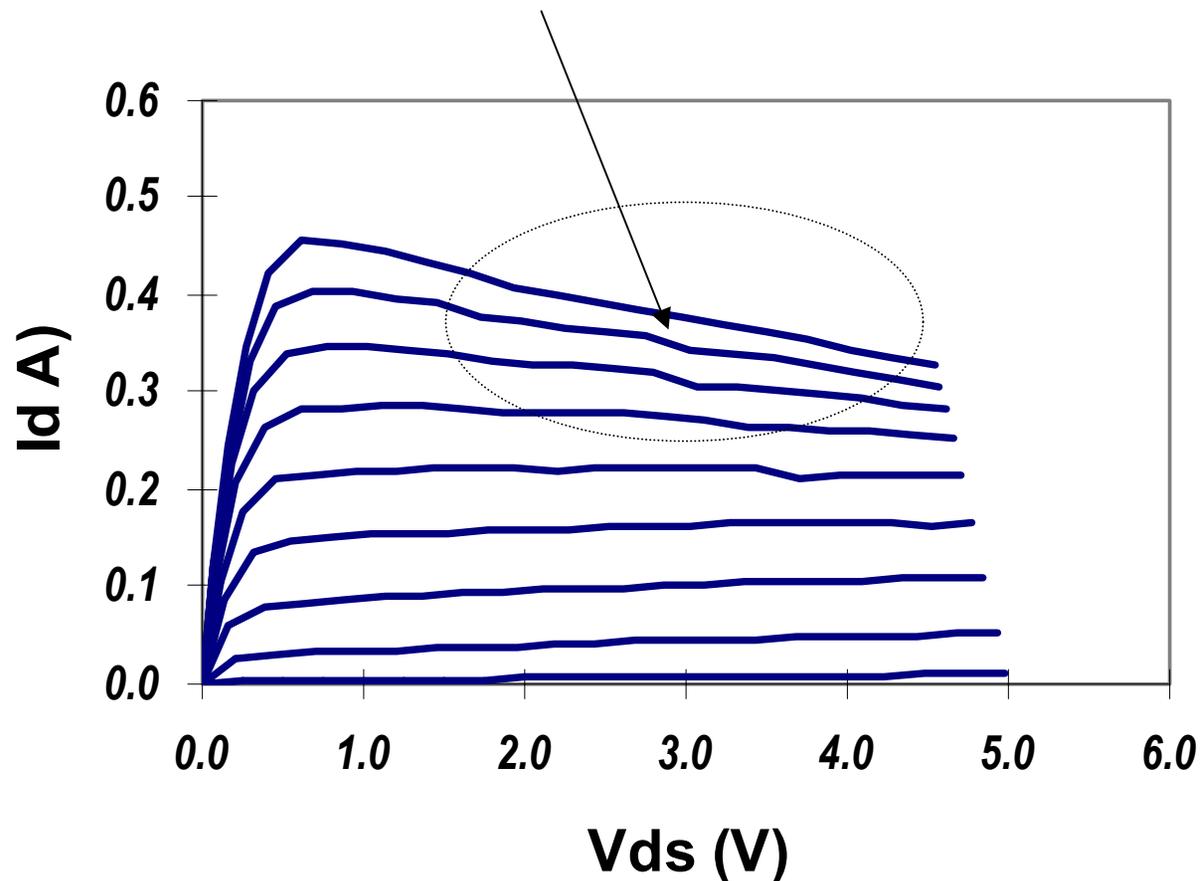
- PHEMT/HBTs feature higher efficiency, high frequency and good linearity and are being widely used in power amplifiers for wireless communications
- Commercial models are difficult to predict consistent small-signal and large-signal power performance including linearity.

The requirements for a good model are:

- Must be capable of reproducing three-terminal dc IV curves over wide range and possible IV collapses
- Must be capable of fitting measured S-parameters over a wide bias range
- Must accurately predict power, efficiency and linearity
- Must be able to predict load-pull behavior
- Must be scaleable to large-size used in power amplifiers
- Good convergence

# PHEMT modeling issue: Self-heating

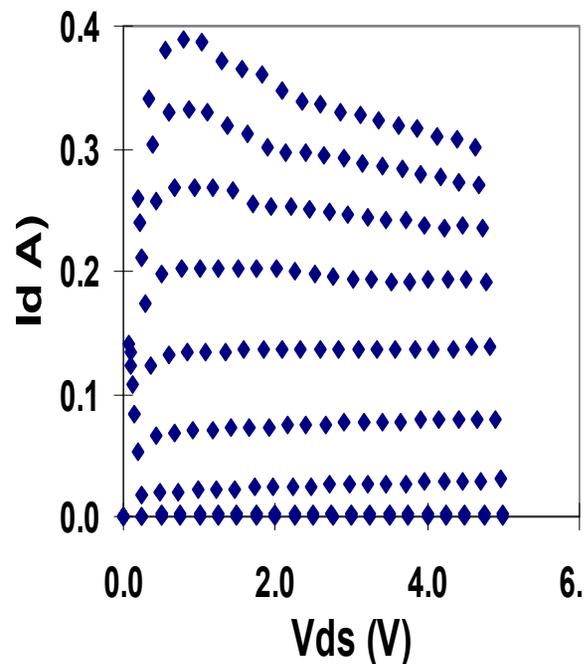
- Positive RF Gds but Negative DC Gdso at Higher Power Dissipation Region



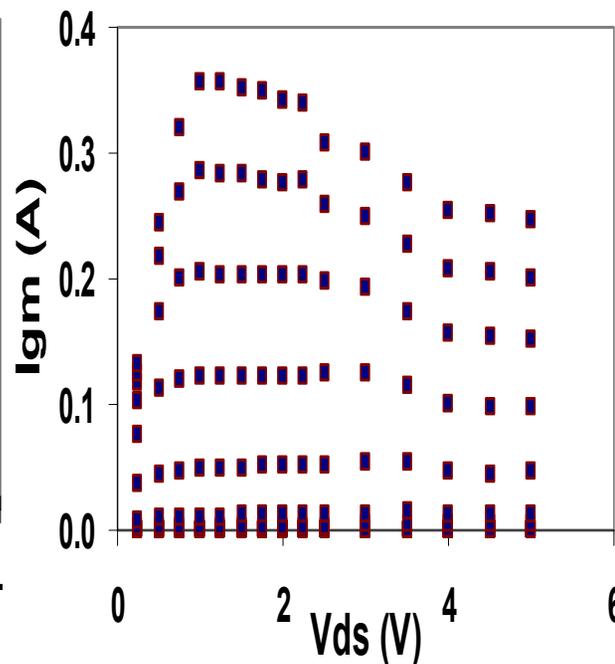
# PHEMT modeling issue: I-V dispersion

- DC-IV Does Not Mean Equal to RF-IV
- RF IVs That Fit RF Gm and RF Gds Differ From Each Other

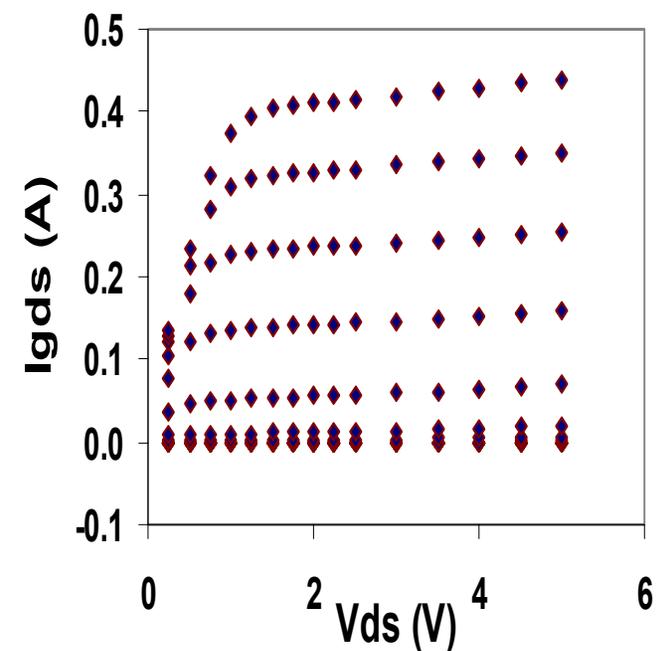
DC IV



RF IV That Fits RF Gm



RF IV That Fits RF Gds



# PHEMT modeling issue: Charge Conservation?

- 2d-charge  $Q_g$  Can Be Integrated From Extracted (Based on Measurement Data)  $C_{gs}(v_{gs}, v_{gd})$  and  $C_{gd}(v_{gs}, v_{gd})$  and Should Be Path-independent

## Charge Conservation or Path Independence

Rule Requires:

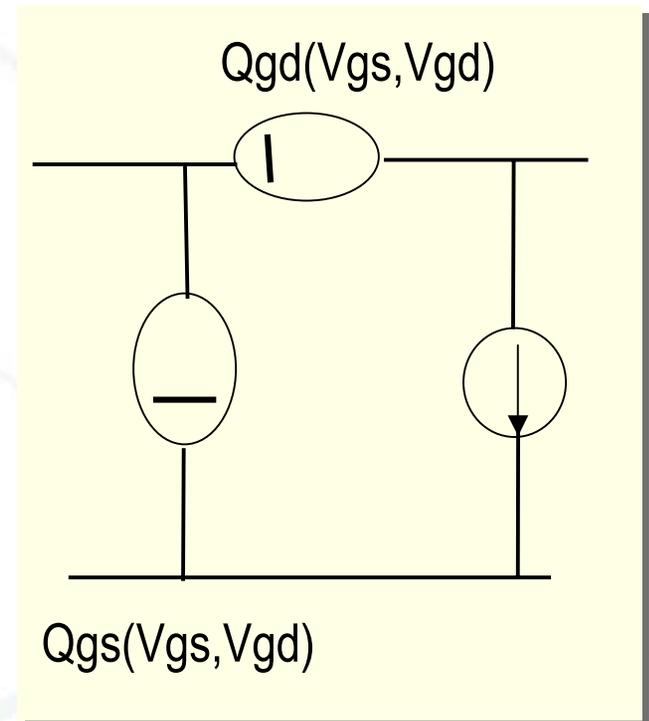
$$Q_g = \int (C_{gs} dv_{gs} + C_{gd} dV_{gd} )$$

$$\frac{\partial C_{gs}}{\partial V_{gd}} = \frac{\partial C_{gd}}{\partial V_{gs}}$$

For Small Size Devices and No Significant Dispersion, Path Independence Does Hold. In general, it does not hold, because of improper equivalent circuit

# PHEMT modeling issue: consistence and others

- A derived small-signal model from the large-signal model must be consistent with small-signal models over a wide range of biases
- 2D QV Functions in Large-signal Model  
Introduce Additional Trans-capacitances that do not exist in small-signal models
- Be continuous up to at least third derivatives of IV and QV curves
- Accurate gate current model including leakage and breakdown

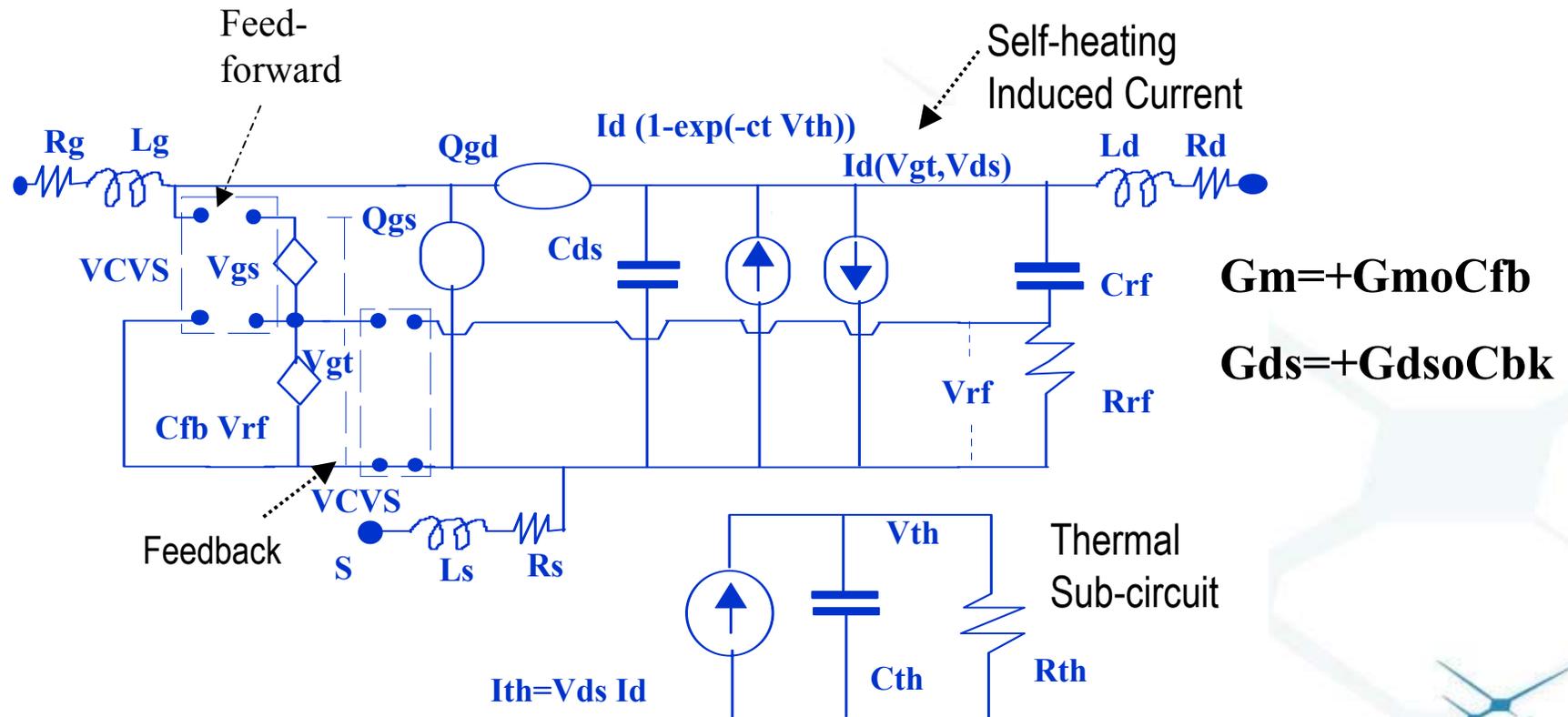


# Empirical model verses Table-based model

- Both models use simple  $\Pi$ -shaped intrinsic equivalent circuit
- Both models use IV and QV characteristics and assume path-independence
- Both models use simple linear or nonlinear RC-type circuit on drain side to account for low-frequency dispersion
- Empirical models have advantages of approximate mapping onto device physical structure, large-dynamic range independent of measurement range. Their disadvantage is accuracy.
- Table-based models have advantages of least-parameter-extraction, technology-independence, accuracy but the disadvantages are: slower convergence, limited validity in its measurement range in extraction.

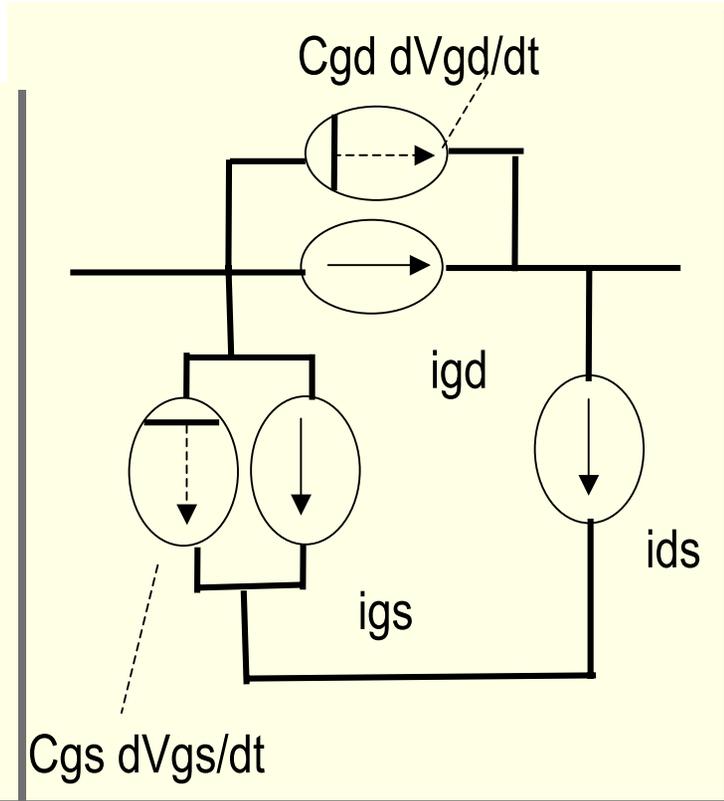
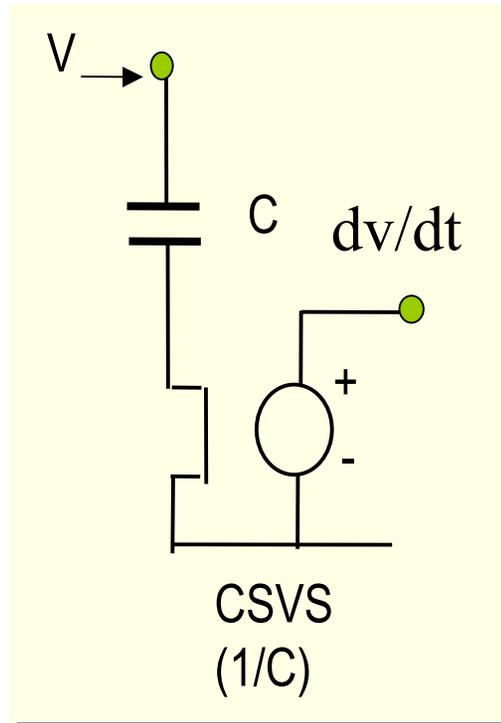
# Dispersion model of PHEMTs

- Instead of Using RC Branch in Drain Port, Alpha Model Uses a Feed-back and Feed-forward Circuit to Modify the RF Gds and RF Gm.
- Self-heating Effects Are Modeled by a Sub-thermal-circuit and a Coefficient of Id Modification



# 'No-Charge' model

- Use Capacitive Current Sources to Replace Charge Sources
- Create a Virtual Node (Voltages  $dv\_dt$ ) That Are Proportional to Time-derivative of  $V_{gs}$  or  $V_{gd}$ . The Capacitance Current,  $C(V_s) \cdot dV\_dt$ , Is the Nonlinear Function of  $V_{gs}$ ,  $v_{gd}$  and  $dV\_dt$

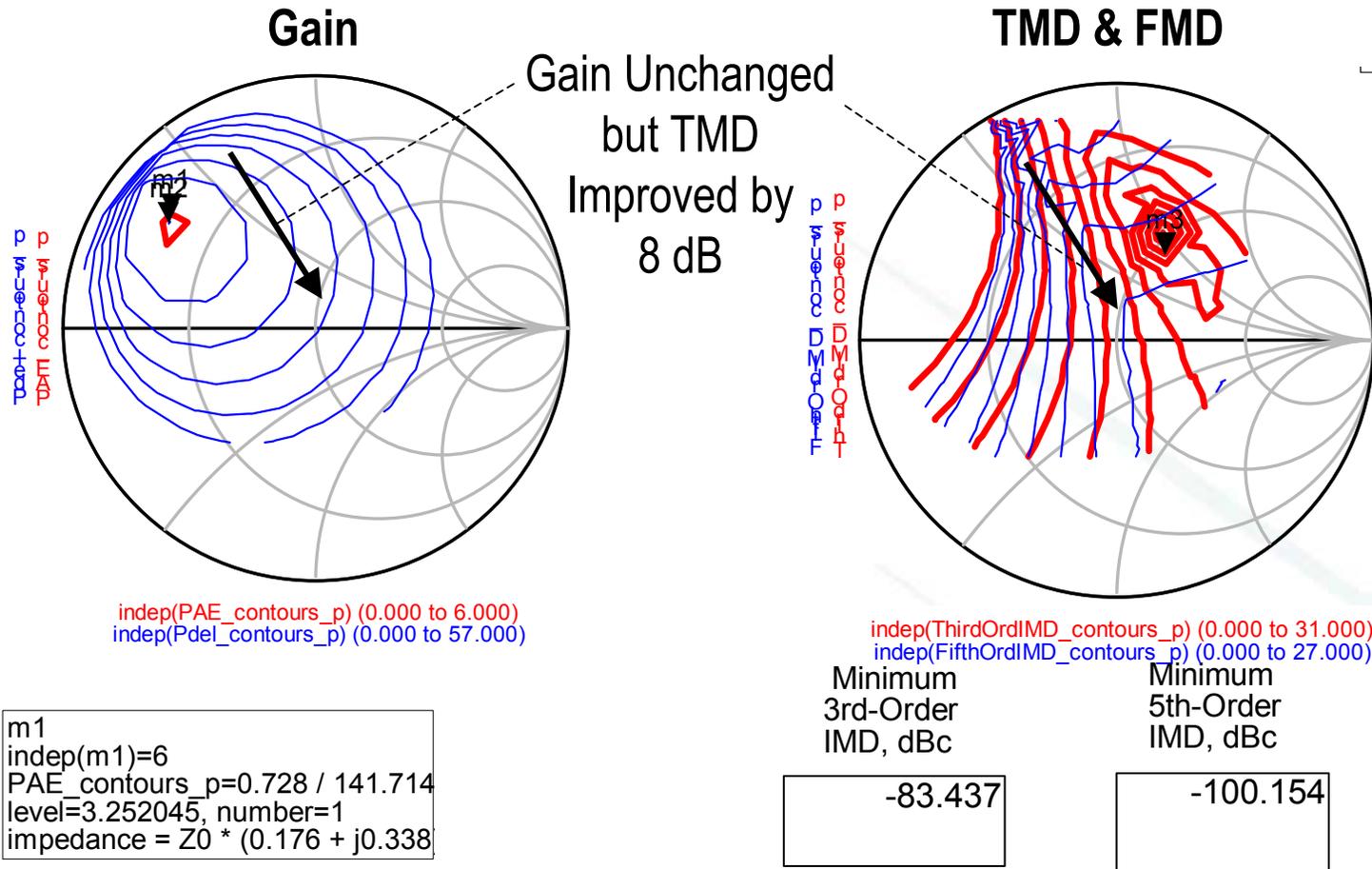


# Charge model verses 'Non-charge' model

- No extra trans-capacitances are involved
- Complete and one-by-one-correspondence consistence with small-signal models over all bias-points measured
- Care must be taken to avoid average component of capacitive currents. Use CR broke circuit for each current
- Charge model is still better in convergence.
- Both models can be table-based or empirical.

# Application: 2-tone Load-pull Simulation

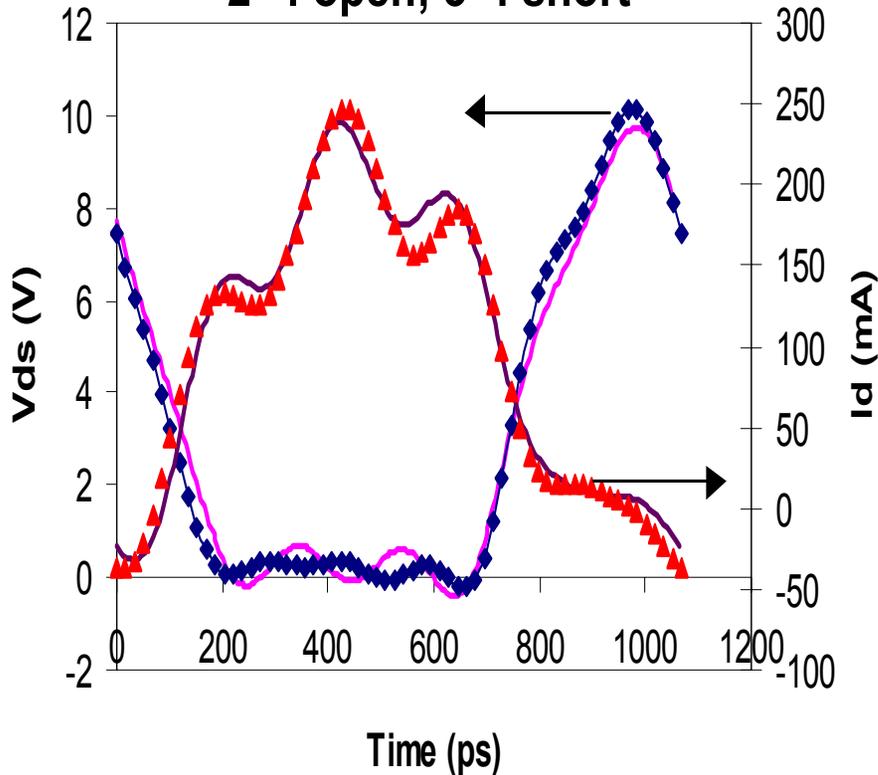
- The Results Are Verified by Comparing the Measured at Several Points



# Application: Waveform at Inverse-F and Class-F Operation

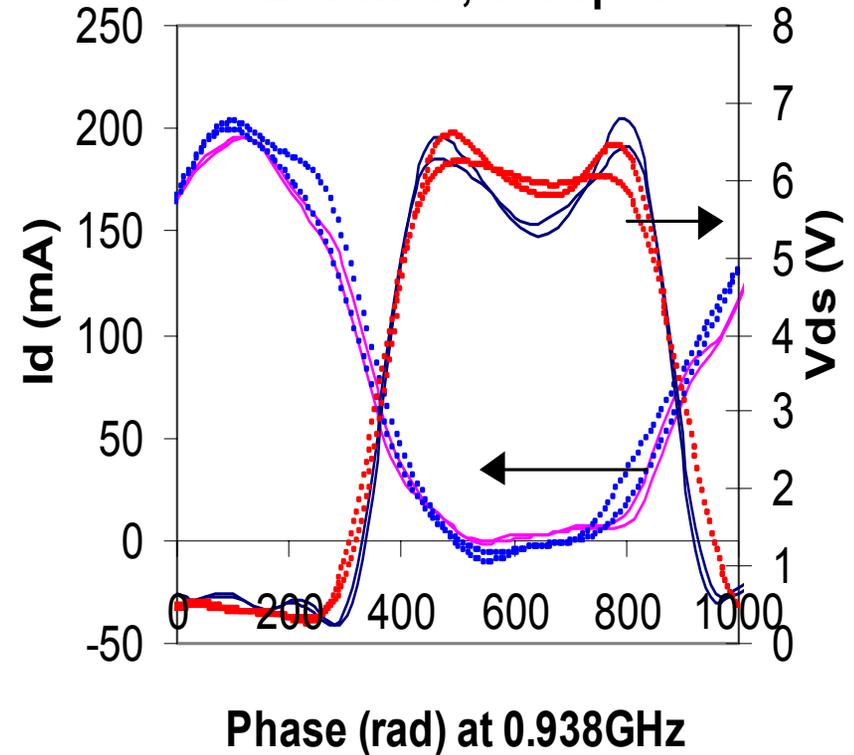
## Class Inverse-F (PAE 80%)

2<sup>nd</sup>: open; 3<sup>rd</sup>: short



## Class F (PAE 69%)

2<sup>nd</sup>: short; 3<sup>rd</sup>: open



Symbol: Measured

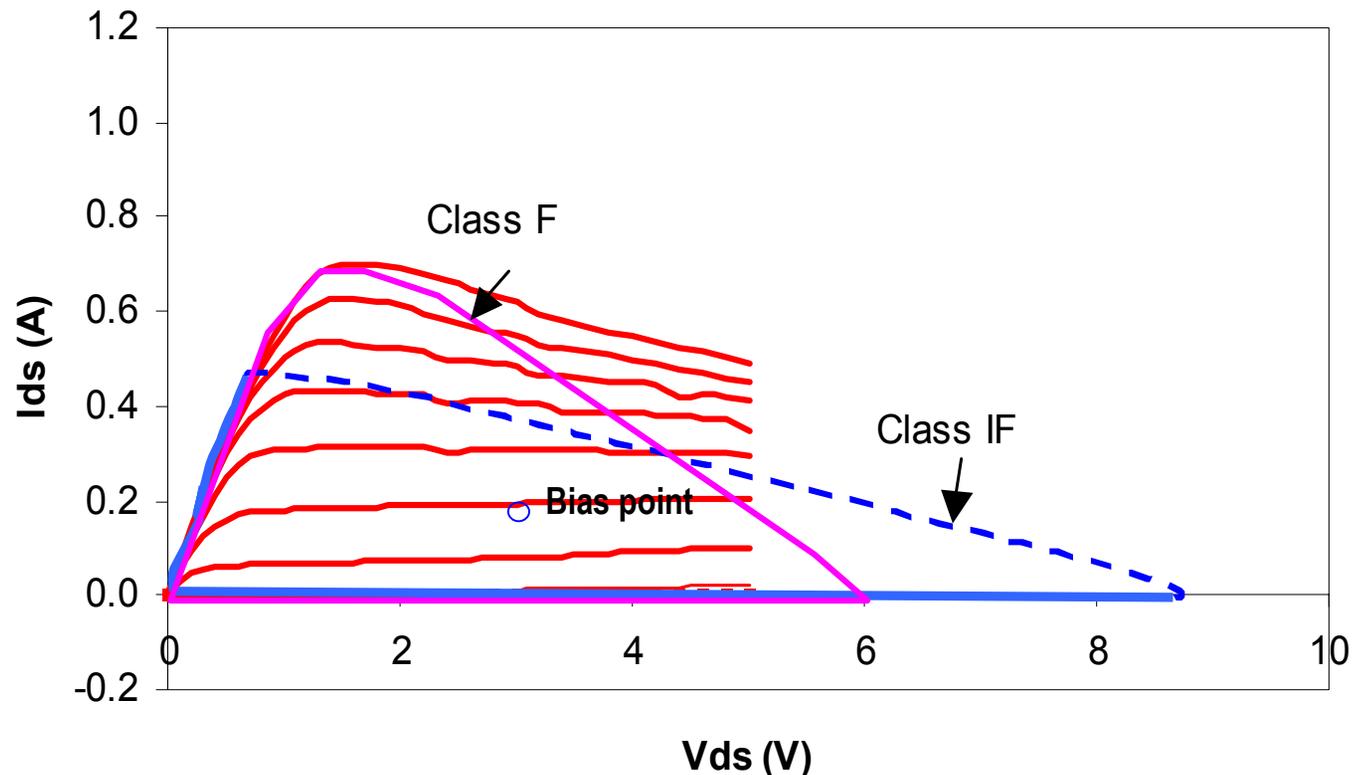
Line: Modeled

$V_{ds} = 3.2$  V  $V_g = -0.88$  V (Inverse F),  $V_g = -1.1$  V (Class-F), Total Wg = 2 mm

# Application: load-line of ideal Inverse-F and Class-F Operation

High PAE Requirement: -  $I_d \approx 0$  when  $V_d$  swings,  $V_d$  minimized, when  $I_d$  swings  
- fast transit for  $I_d * V_d \neq 0$  (broken line)

Class F: visit more time on resistive loss area than class inverse-F



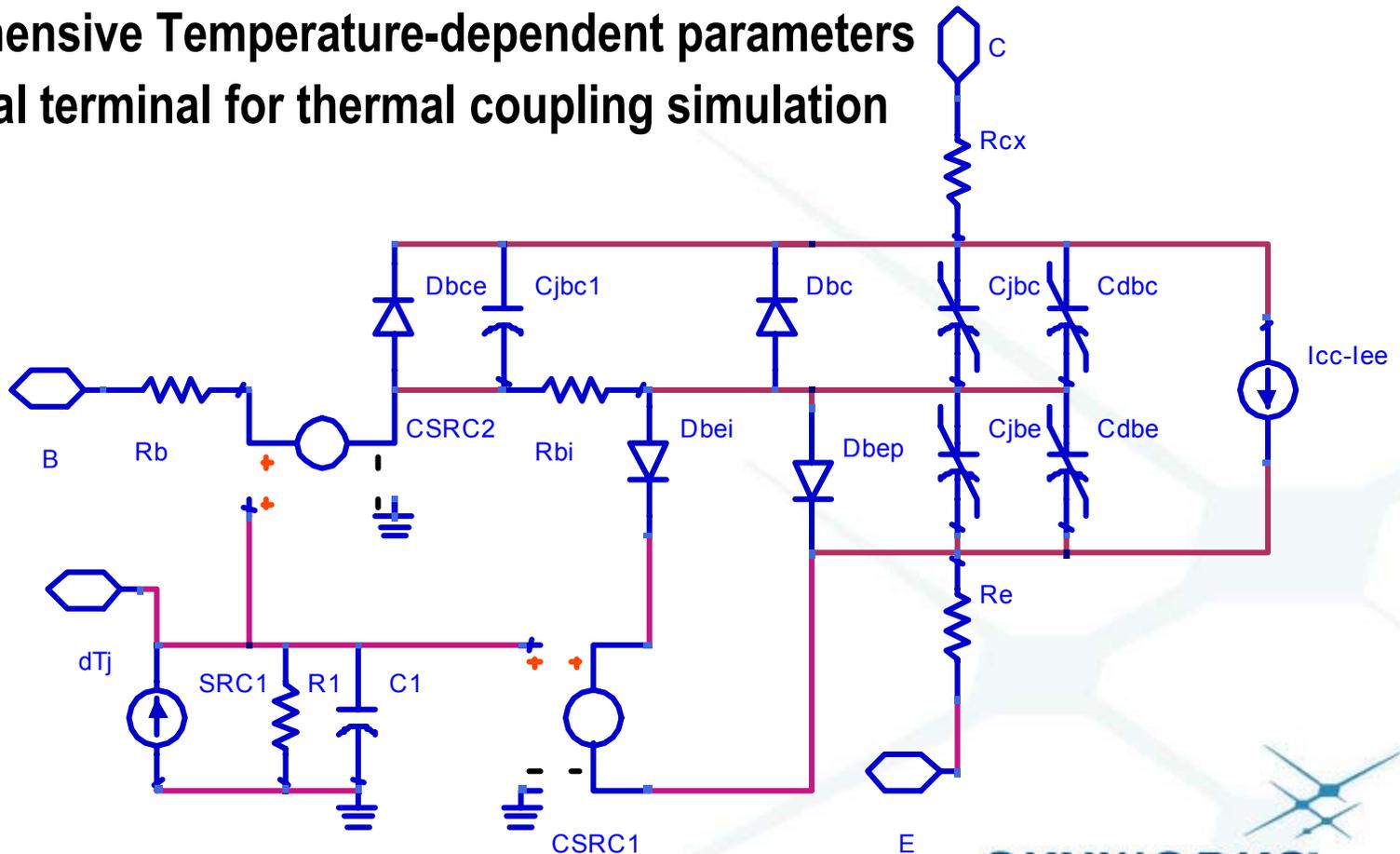
# HBT modeling

- **Most hand-set PA's are using HBTs**
- **The advantages over PHEMTs: unipolar DC supply, uniformity and high yield, linearity. Caution must be taken on thermal management**
- **Commercial and non-commercial models**
  - **Commercial models: GP, ✓ VBIC, Mextram, Hicem**
  - **Non-commercial models: ✓ Modified-GP, ✓ Modified-VBIC or others**



# Modified GP model and features

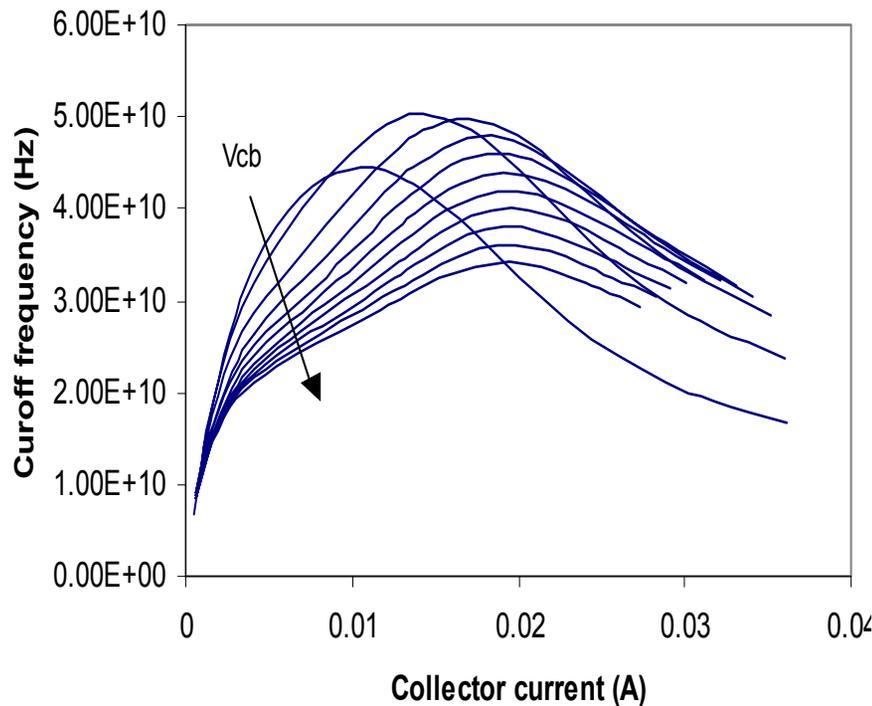
- ✓ major Self-heating effects including nonlinear terms
- ✓ Separation of the transfer current and base current
- ✓ Comprehensive Temperature-dependent parameters
- ✓ Additional terminal for thermal coupling simulation



# Tf and Cbc characteristics that commercial models can not fit

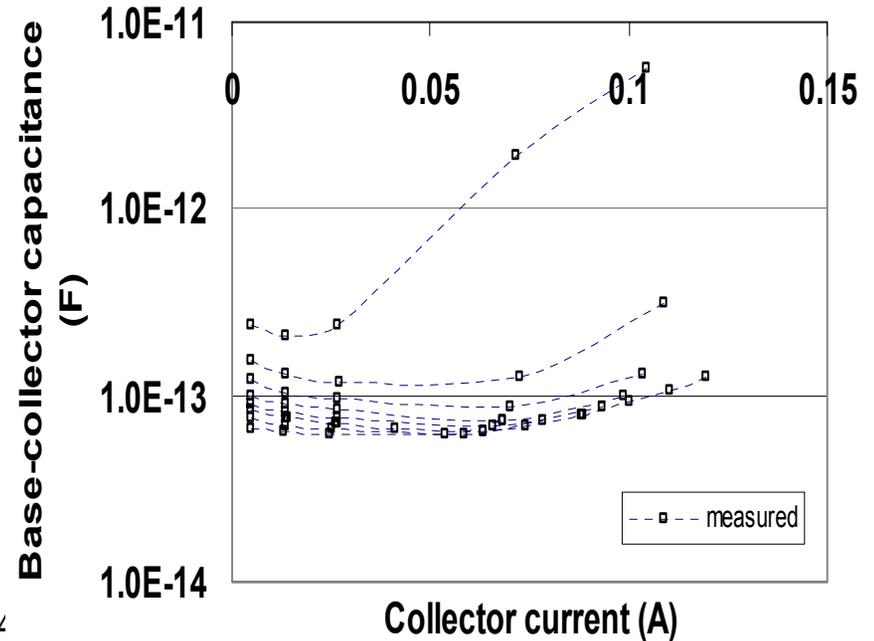
Ft as function of Vcb & Ic

Vcb=-0.8, & -0.5 to 4 V step 0.5 V



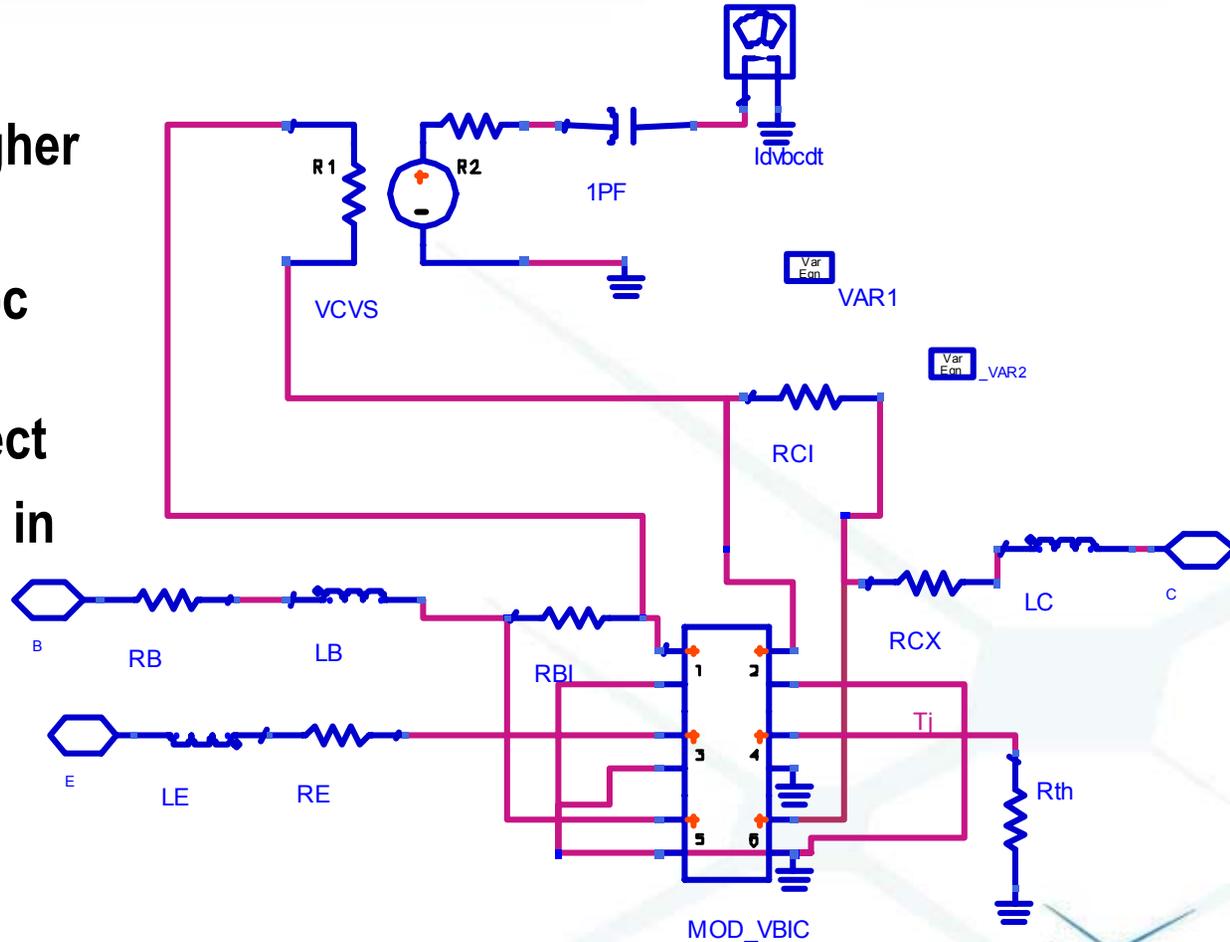
Cbc as function of Vbc & Ic

Vbc=0.5 to 3.5 V step 0.5 V



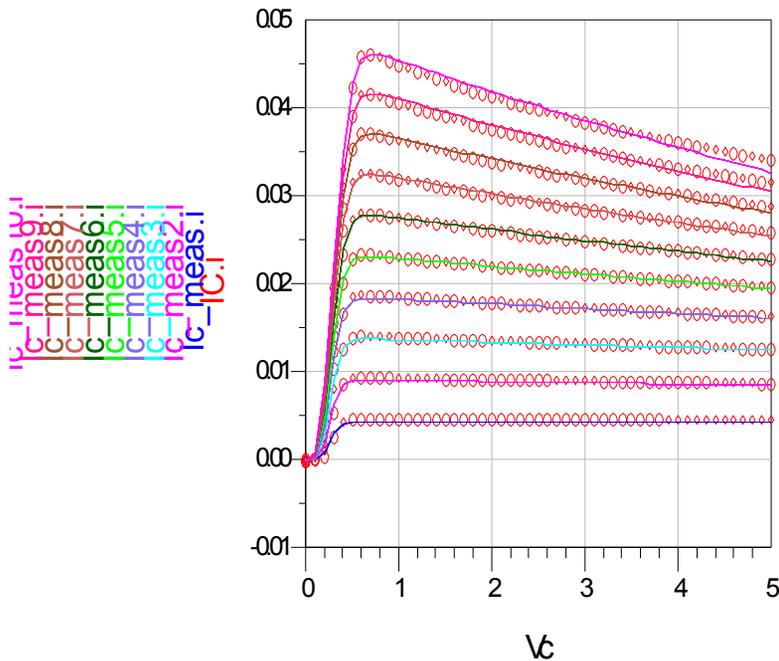
# Modified VBIC model and features

- ✓ Self-heating
- ✓ accurate  $T_f$  model to account for  $f_t$  drop at higher current (Kirk Effect)
- ✓  $V_{bc}$  &  $I_c$  dependent  $C_{bc}$  due to mobile-charge modulation and Kirk Effect
- ✓ Implemented with SDD in ADS



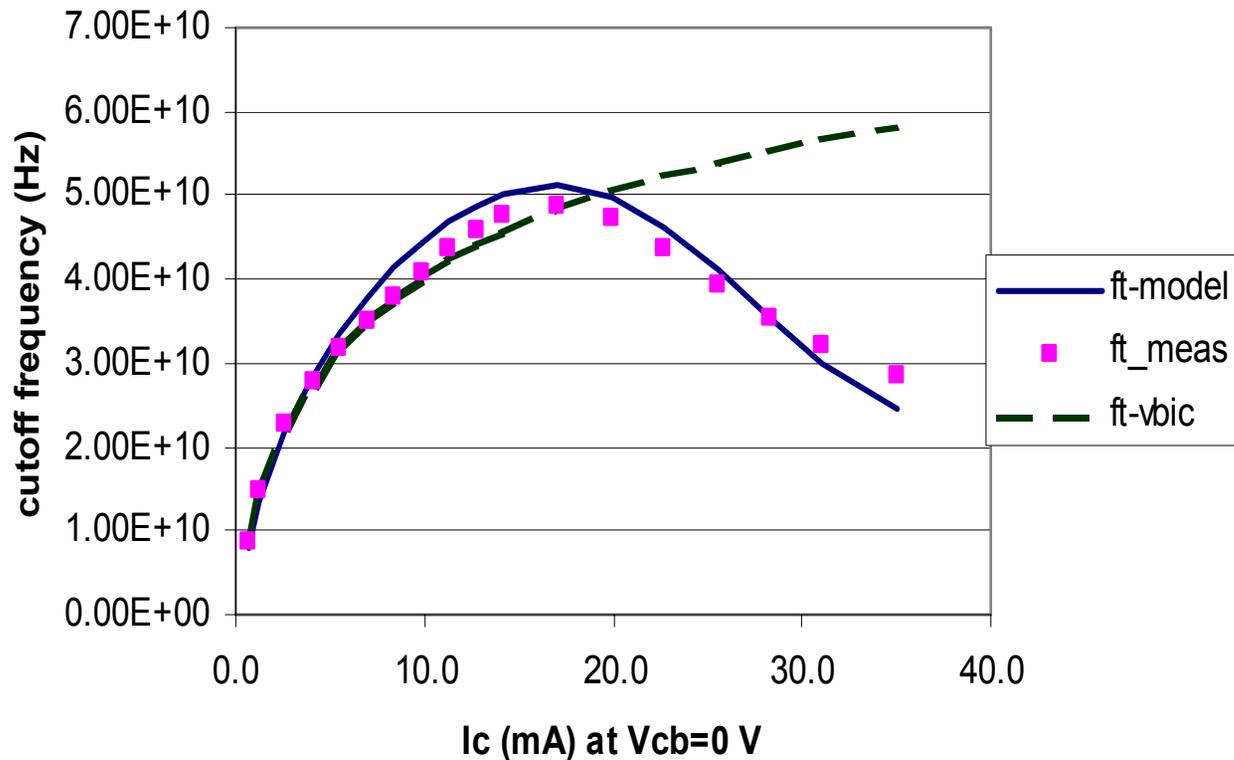
# Ic-Vc and Vb-Vc curves at constant Ib modeled vs measured

$A_e=56\mu\text{m}^2$  Ic-Vc



# Modified VBIC fits ft at higher current

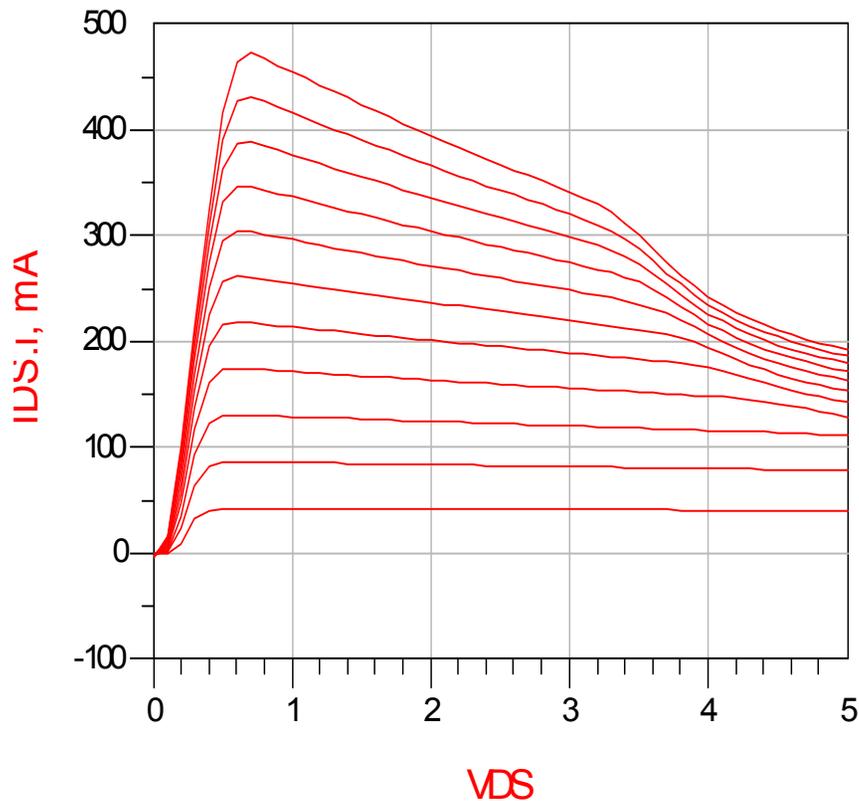
Ft as function of  $V_{cb}$  &  $I_c$   $V_{cb}=0V$  Solid line:  
Modified VBIC Broken line: VBIC model



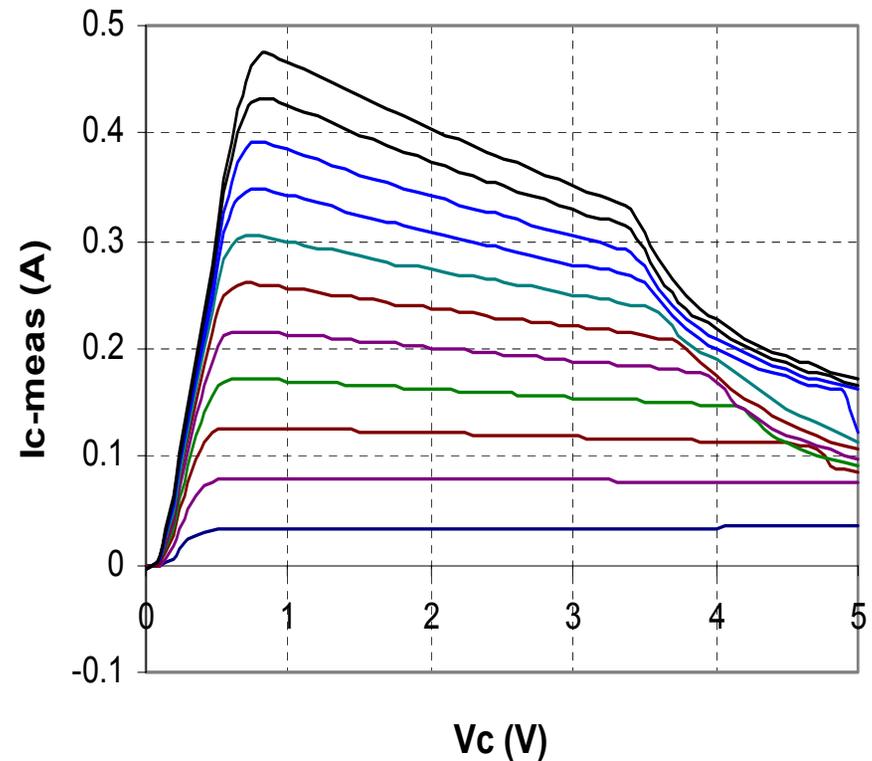
# IV collapse modeled vs measured

$A_e=960 \text{ um}^2$   $I_b=0.4\text{mA}$  to  $4.4 \text{ mA}$  step  $0.4\text{mA}$

simulated



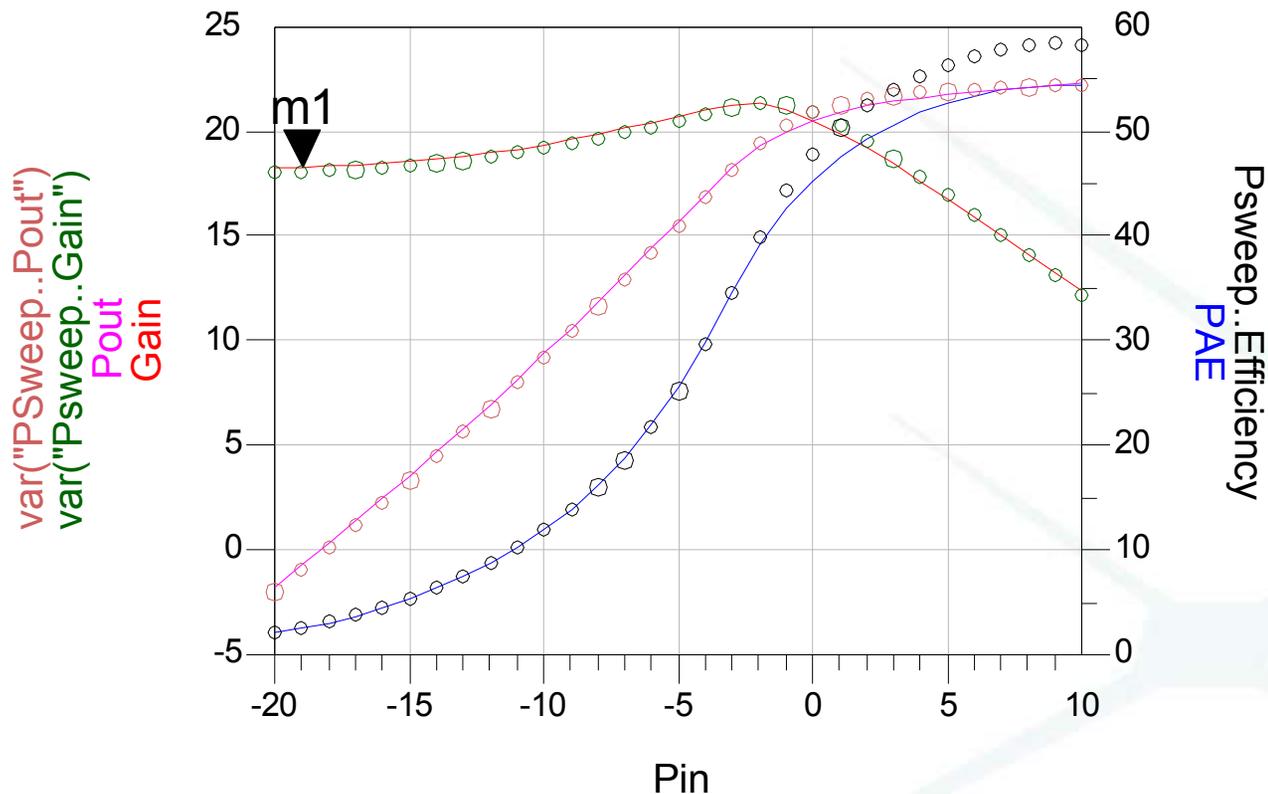
measured



# Power performance Modeled vs Measured

V27 H1503-901 720um<sup>2</sup> Vc=3.2V Ic=7.54mA

Pin=-19.000  
Gain=18.283

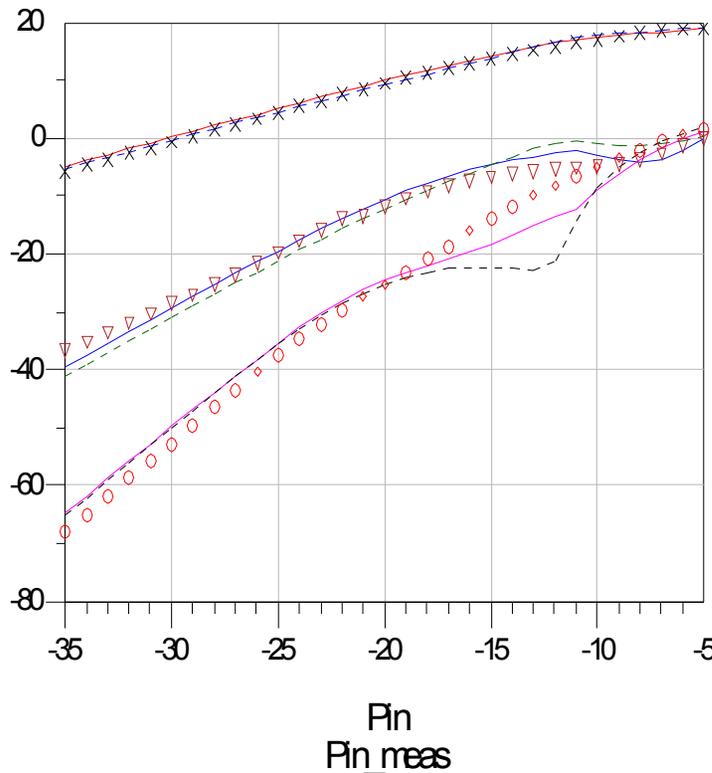


# Harmonics performance Modeled vs Measured

V27 H1503-901 60um<sup>2</sup> Vc=3.5V Ic=7mA

```

var("datasetName...3F1")
var("datasetName...2F1")
datasetName: POut_meas
LoadPul1-VBIC...3
LoadPul1-VBIC...2
LoadPul1-VBIC...1
f2
f1
    
```



Vc=3.5 V Vb=1.357 V

Ic=6.98 mA

Rbext=600ohm

Source: f1: 0.78 ∠26.7

F2: 0.6 ∠6.8

F3: 0.17 ∠168

Load: f1 0.32 ∠26.7

F2: 0.77 ∠-88.4

F3: 0.67 ∠-137.5

Symbol:measured, solid line:new model, broken lin:VBIC

# IM3 & IM5 performance Modeled vs Measured

V27 H1503-901 60um<sup>2</sup> Vc=3.5V Ic=7mA

Vc=3.5 V Vb=1.357 V

Ic=6.98 mA

Rbext=600ohm

Source: f1: 0.78 ∠26.7

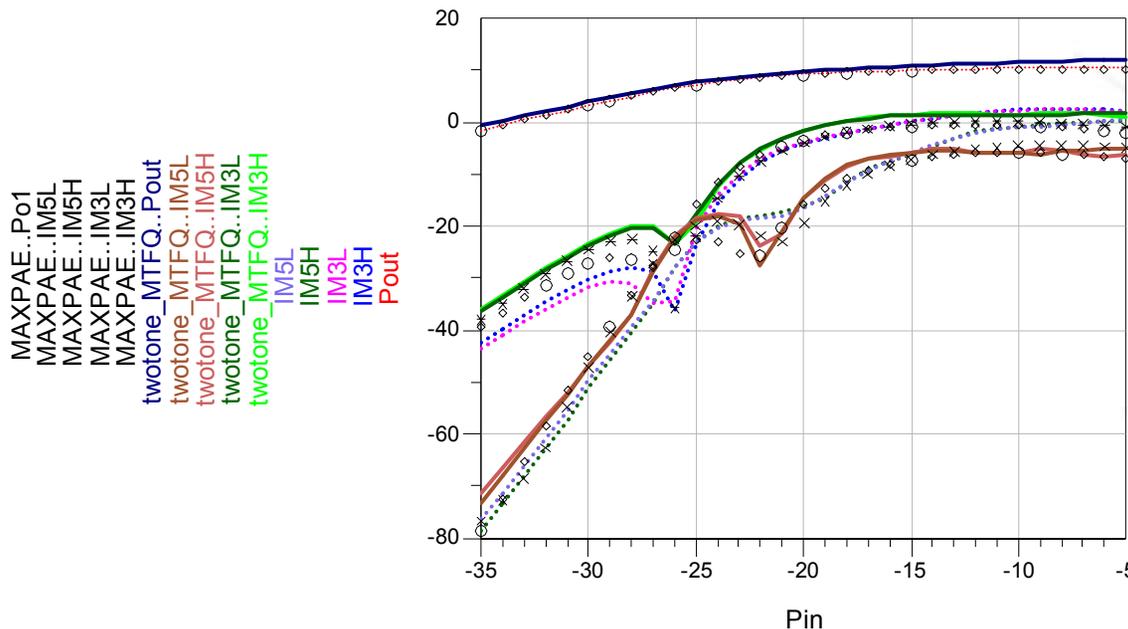
F2: 0.6 ∠6.8

F3: 0.17 ∠168

Load: f1 0.32 ∠26.7

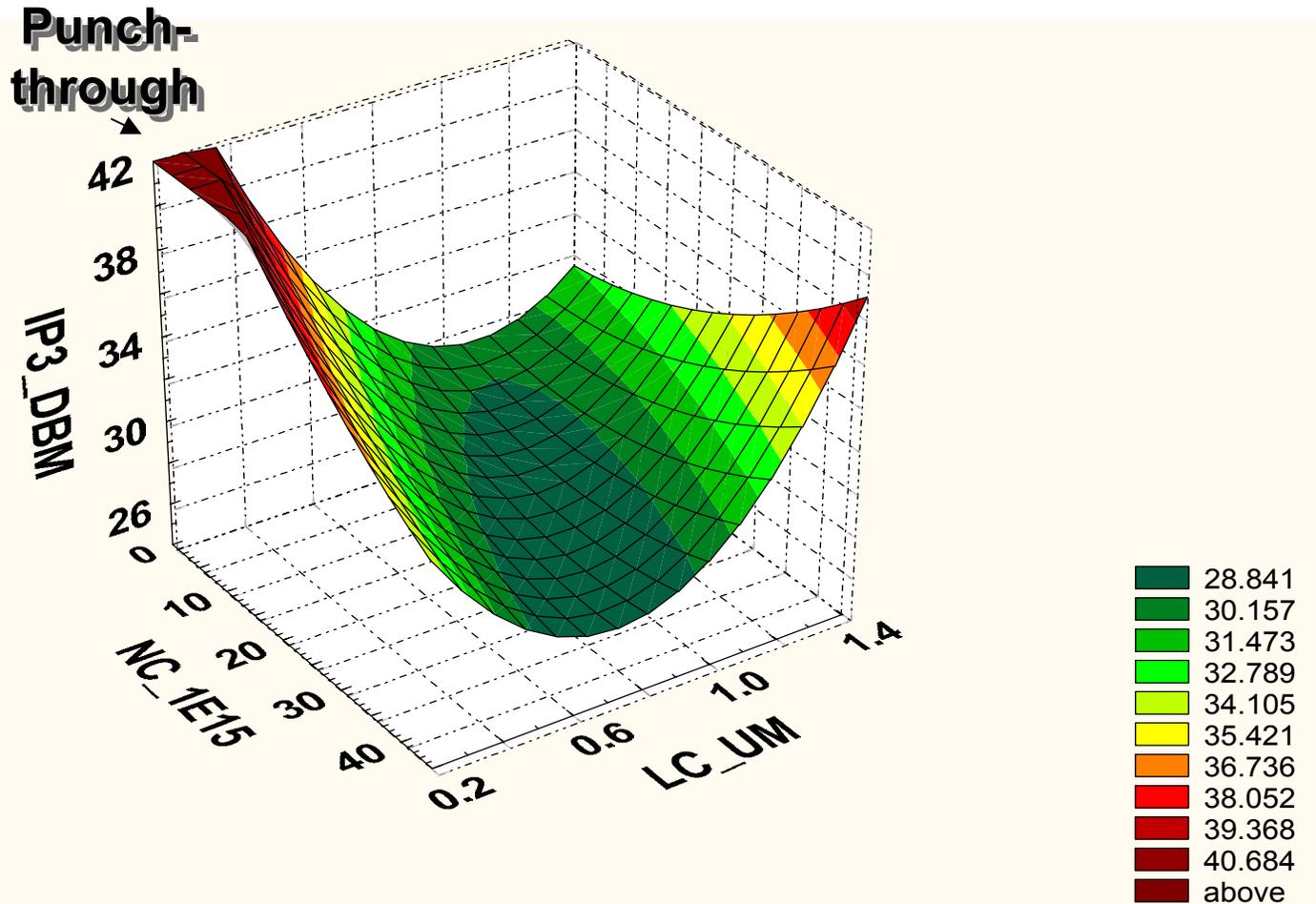
F2: 0.77 ∠-88.4

F3: 0.67 ∠-137.5



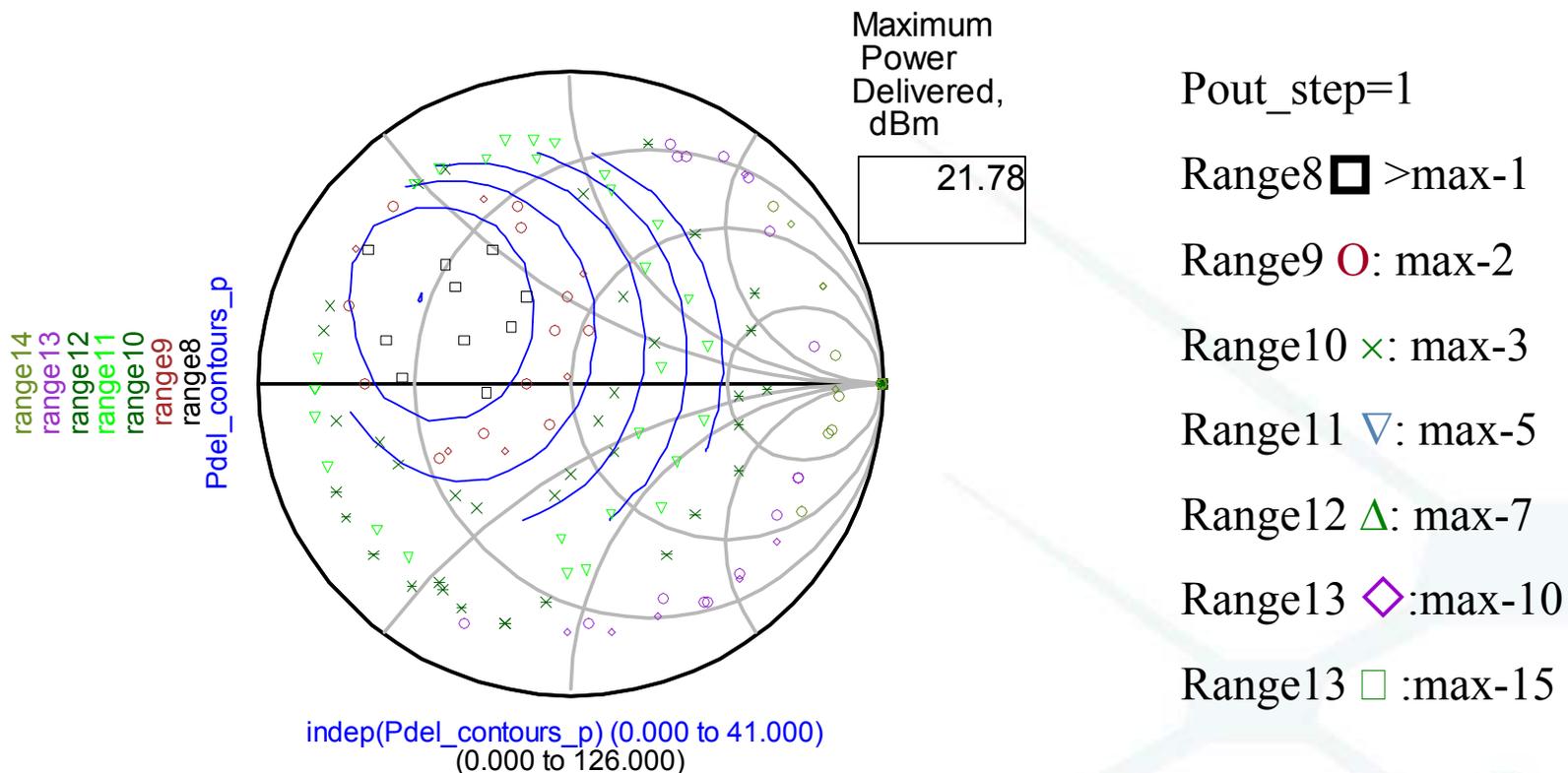
Symbol:measured, solid line:new model, broken lin:VBIC

# Linearity improves for punch-through structure



# Pout load-pull, Modeled vs Measured

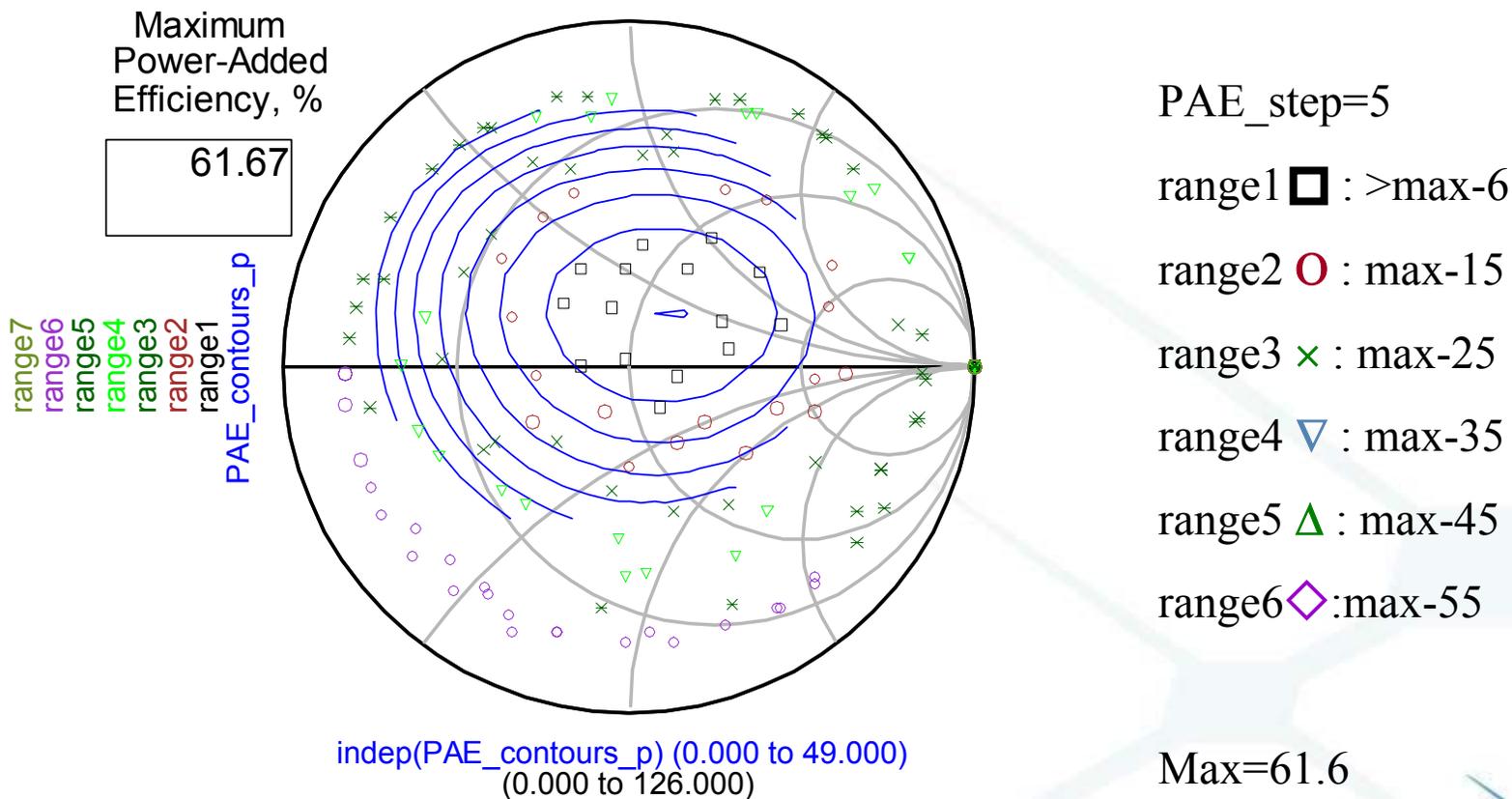
V27 H1503-901 720um<sup>2</sup> Vc=3.2V Ic=37mA  
 Pin=0dBm Gamm(2)=0.52<-117



Max=21.4

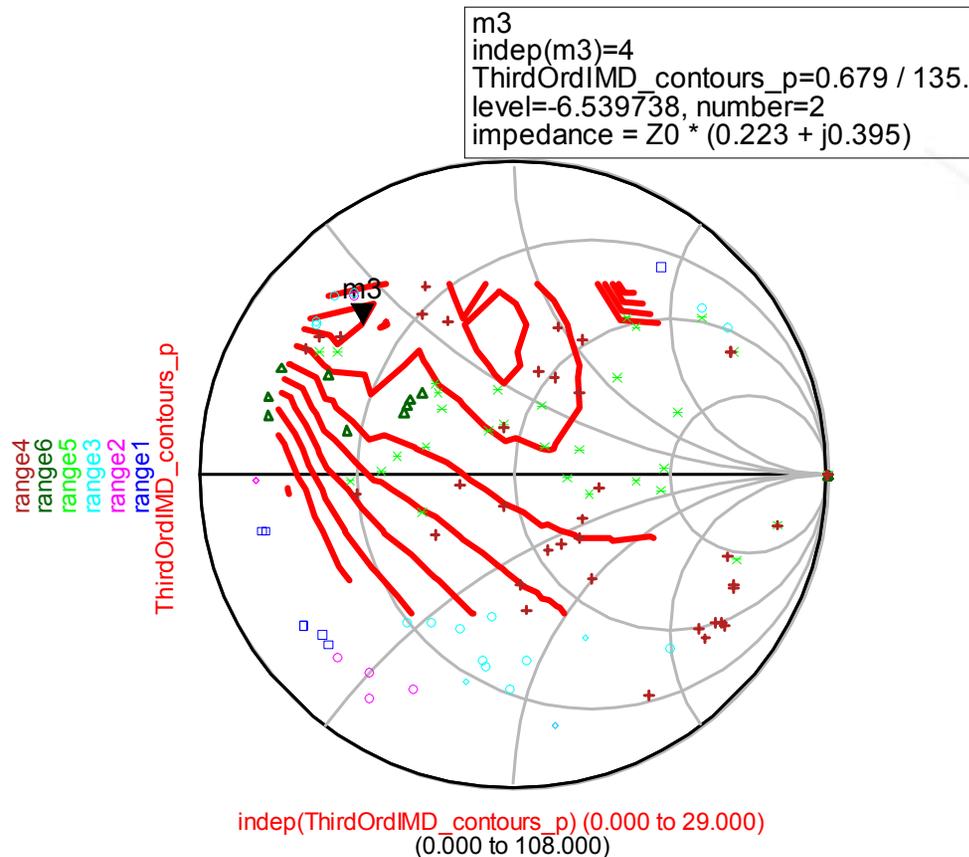
# PAE load-pull, Modeled vs Measured

V27 H1503-901 720um<sup>2</sup> Vc=3.2V Ic=37mA  
Pin=0dBm Gamm(2)=0.52<-117



# IM3 load-pull, Modeled vs Measured

V27 H1503-901 720um<sup>2</sup> Vc=3.2V Ic=37mA  
Pin=0dBm Gamm(2)=0.52<-117



IM3\_modeled\_step=2

range1  $\square$  : -18  $\rightarrow$  -16

range2:  $\circ$  -16  $\rightarrow$  -14

range3  $\nabla$  : -14  $\rightarrow$  -12

Range4  $+$ : -12  $\rightarrow$  -10

Range5  $\times$ : -10  $\rightarrow$  -8

Ranger6  $\times$ :  $>$ -8

# PAE load-pull for 2<sup>nd</sup> harmonic, Modeled vs Measured

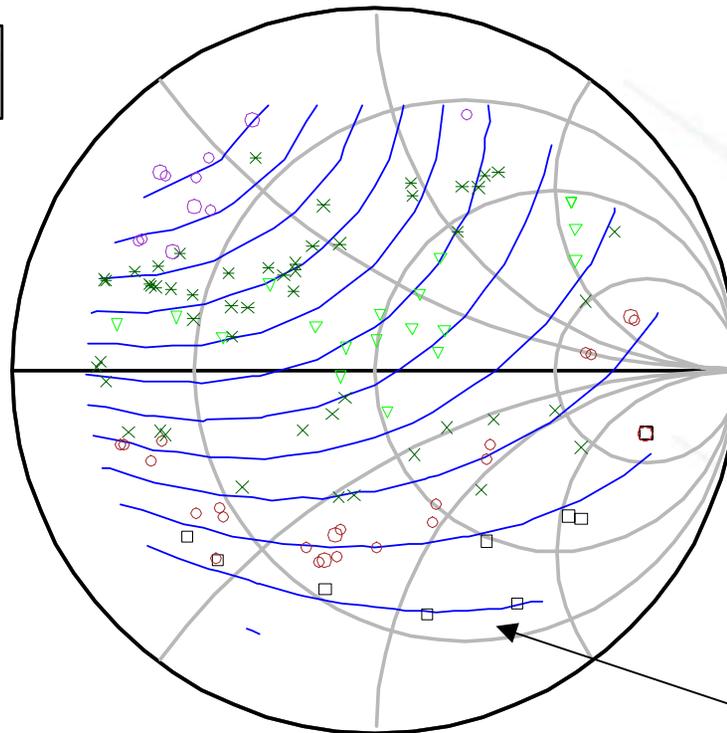
V27 H1503-901 720um<sup>2</sup> Vc=3.2V Ic=37mA  
Pin=3dBm Gamm(1)=0.558<111

No obvious difference of class F and inverse-F!

Maximum Cal.  
PAE, %

60.99

range7  
range6  
range5  
range4  
range3  
range2  
range1  
PAE\_contours\_p



indep(PAE\_contours\_p) (0.000 to 24.000)  
(0.000 to 126.000)

PAE\_modeled\_step=2.5

range1  $\square$ : max-3  $\rightarrow$  max

range2  $\circ$ : max-6  $\rightarrow$  max-3

range3  $\times$ : max-10  $\rightarrow$  max-6

range4  $\nabla$ : max-15  $\rightarrow$  max-10

range5  $\triangle$ : max-20  $\rightarrow$  max-15

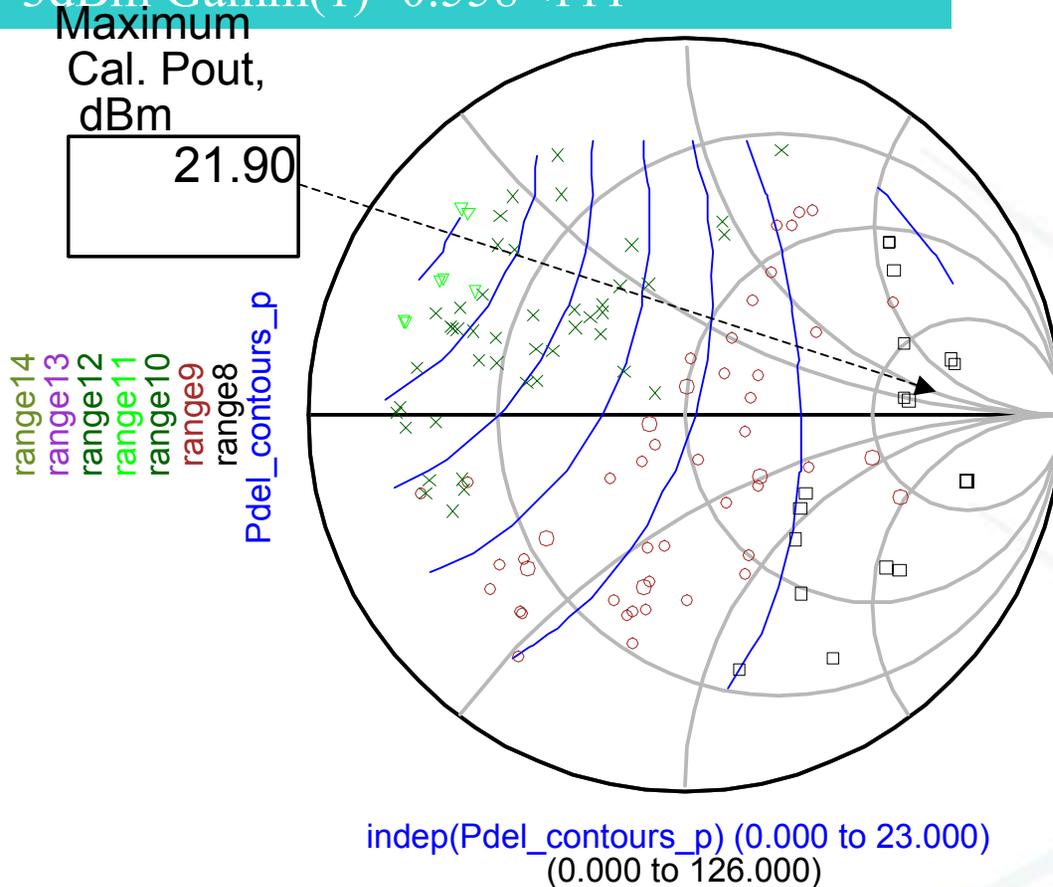
range6  $\diamond$ : <max-20

Max=56.7

# Pout load-pull for 2<sup>nd</sup> harmonic, Modeled vs Measured

V27 H1503-901 720um<sup>2</sup> Vc=3.2V Ic=37mA  
Pin=3dBm Gamm(1)=0.558<111

For Pout inverse-F is better than class F!



Pout\_modeled\_step=0.5

Range8 □ 19.9→20.9

range9 ○ : 18.9→19.9

range10 × : 17.9→18.9

range11 ▽ : 15.9→17.9

range12: 13.9→15.9

range13: 10.9→13.9

range13: <10.9

# IM3 load-pull for 2<sup>nd</sup> harmonic, Modeled vs Measured

V27 H1503-901 720um<sup>2</sup> Vc=3.2V Ic=37mA  
 Pin=3dBm Gamm(1)=0.558<111

For IM3 inverse-F is also better than class F!

m1  
 indep(m1)=3  
 ThirdOrdIMD\_contours\_p=0.736 / 19.224  
 level=-10.834816, number=1  
 impedance = Z0 \* (3.019 + j3.197)

IM3\_modeled\_step=0.5

range1  $\blacksquare$  : -13 → -12.5

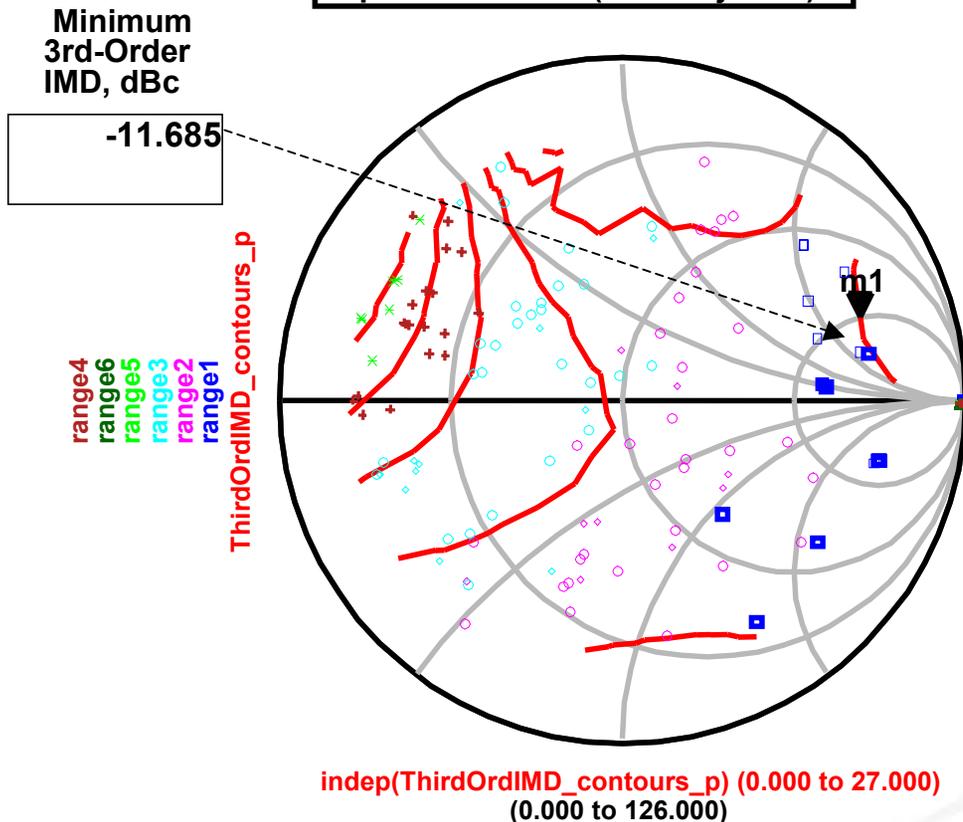
range2  $\circ$  : -12.5 → -12

range3  $\blacktriangledown$  : -12 → -11

Range4 + : -11 → -10

Range5 x : -10 → -8

ranger6: >-8



# Conclusion

- The problems with conventional large-signal PHEMT models are addressed that include: dispersion, 'non-charge-conservation' originated from use of simple equivalent circuit, etc
- Dispersion and 'no-charge' models are presented that overcome the difficulties
- The issues in HBT modeling in terms of mobile charge-modulation and Kirk effects are addressed and modified MP and VBIC models are presented
- The models are verified with comprehensive load-pull results
- Class inverse-F with 2<sup>nd</sup> harmonic tuned at high impedance is recommended for PHEMT PA design due to its higher PAE over class-F and is likely useful due to its better linearity for HBT power amplifiers.

# Acknowledgement

- Dr. Gene Tkachenko, Dr. Ding Dai for his support
- Significant contribution by Dr. G. Tkachenko, A. Klimashov, J. Gering and D. Bartle